22nd RD50 Workshop (Albuquerque, USA)

Tuesday 4 June 2013

Session 3:: Simulations and Charge Multiplication - **Student Union Building (09:00 - 14:00)**

   -Conveners: Alexandra Junkes

time	[id] title	presenter
09:00	[0] Simulation of Double Junction in Irradiated Detectors Using Silvaco TCAD	Mrs GOLOVLEVA, Maria
09:20	[7] Simulation of CV, TCT and CCE with an effective 2-defect model (moved to Wednesday)	EBER, Robert
09:25	[48] p-n-n+ diode CV characteristics changes at various contract and body doping concentrations. TCAD simulations	Prof. VAITKUS, Juozas
09:40	[38] Simulations of edge-TCT and 2-defect model CCE	PELTOLA, Timo Hannu Tapani
10:00	Coffee break	
10:30	[4] Simulation and Technology developments of Low Gain Avalanche Detectors (LGAD) for High Energy Physics applications	Dr HIDALGO, Salvador
10:45	[44] Red TCT measurements of Low Gain Avalanche Diodes (LGAD) produced at CNM-Barcelona	FERNANDEZ GARCIA, Marcos
11:00	[33] Simulation of Gain-Optimized Sensors	PARKER, Colin
11:20	[13] Pulse shapes of alpha particles in CNM diodes with and without gain	ELY, Scott
11:40	[28] Studies of CNM diodes with gain	KRAMBERGER, Gregor
12:00	[21] Combined Measurement Results of dedicated RD50 Charge Multiplication Sensors	WONSAK, Sven
12:20	[23] Ultra-Fast Silicon Sensors based on Charge Multiplication, an Update	SADROZINSKI, Hartmut
12:40	Lunch Break	